

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

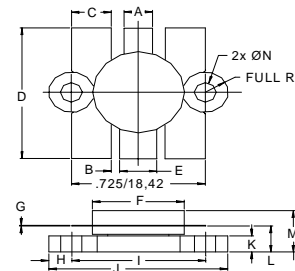
The **ASI 2SC2905** is designed for high power amplifier applications in UHF band.

FEATURES:

- Emitter Ballasted construction.
- $P_G = 4.8$ dB at 45 W/520 MHz
- **Omnigold™** Metalization System
- Common Emitter

MAXIMUM RATINGS

I_C	15 A
V_{CB0}	35 V
V_{CEO}	17 V
V_{CES}	36 V
V_{EBO}	4.0 V
P_{DISS}	120 W @ $T_C = 25^\circ\text{C}$
T_J	-55 °C to +175 °C
T_{STG}	-55 °C to +175 °C
θ_{JC}	1.0 °C/W

PACKAGE STYLE .500 6L FLG


DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.150 / 3.43	.160 / 4.06
B	.045 / 1.14	
C	.210 / 5.33	.220 / 5.59
D	.835 / 21.21	.865 / 21.97
E	.200 / 5.08	.210 / 5.33
F	.490 / 12.45	.510 / 12.95
G	.003 / 0.08	.007 / 0.18
H	.125 / 3.18	
I	.725 / 18.42	
J	.970 / 24.64	.980 / 24.89
K	.090 / 2.29	.105 / 2.67
L	.150 / 3.81	.170 / 4.32
M	.285 / 7.24	
N	.120 / 3.05	.135 / 3.43

CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 1.0$ A	17			V
BV_{CBO}	$I_C = 10$ mA	35			
BV_{EBO}	$I_E = 10$ mA	4.0			V
I_{CBO}	$V_{CB} = 15$ V			2.0	mA
I_{EBO}	$V_{CE} = 3.0$ V			3.0	mA
h_{FE}	$V_{CE} = 10$ V $I_C = 1.0$ A	10		200	---
C_{ob}	$V_{CB} = 12.5$ V $f = 1.0$ MHz			150	pF
P_G	$V_{CE} = 12.5$ V $P_{OUT} = 45$ W $f = 520$ MHz	4.8			dB
η_C		60	65		%